

# SANYO Semiconductors DATA SHEET

## MCH3222 — NPN Epitaxial Planar Silicon Transistor

## **DC / DC Converter Applications**

### **Applications**

· Relay drivers, lamp drivers, motor drivers, flash.

#### **Features**

- · Adoption of FBET, MBIT processes.
- · Large current capacitance.
- · Low collector-to-emitter saturation voltage.
- · High-speed switching.
- Narrow hFE range.
- Ultrasmall package facilitates miniaturization in end products (mounting height: 0.85mm).
- · High allowable power dissipation.

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		100	V
Collector-to-Emitter Voltage	VCES		100	٧
	VCEO		50	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		3	Α
Collector Current (Pulse)	ICP	PW≤1ms	6	Α
Base Current	ΙΒ		600	mA
Collector Dissipation	PC	Mounted on a ceramic board (600mm²x0.8mm)	0.8	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	] Oill
Collector Cutoff Current	ICBO	V <sub>CB</sub> =40V, I <sub>E</sub> =0A			0.1	μΑ
Emitter Cutoff Current	IEBO	VEB=4V, IC=0A			0.1	μΑ
DC Current Gain	hFE	V <sub>CE</sub> =2V, I <sub>C</sub> =100mA	250		400	
Gain-Bandwidth Product	fŢ	V <sub>CE</sub> =10V, I <sub>C</sub> =500mA		380		MHz

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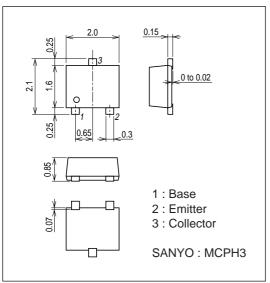
#### MCH3222

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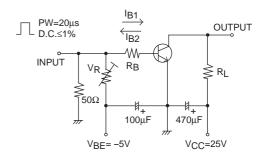
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol	Conditions	min	typ	max	Oill
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		13		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)1	I <sub>C</sub> =1A, I <sub>B</sub> =50mA		60	90	mV
	VCE(sat)2	IC=2A, IB=100mA		100	150	mV
Base-to-Emitter Saturation Voltage	VBE(sat)	IC=2A, IB=100mA		0.88	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0A	100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	IC=100μA, RBE=0Ω	100			V
	V(BR)CEO	IC=1mA, RBE=∞	50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =10μA, I <sub>C</sub> =0A	6			V
Turn-ON Time	ton	See specified Test Circuit.		35		ns
Storage Time	tstg	See specified Test Circuit.		300		ns
Fall Time	tf	See specified Test Circuit.		22		ns

### **Package Dimensions**

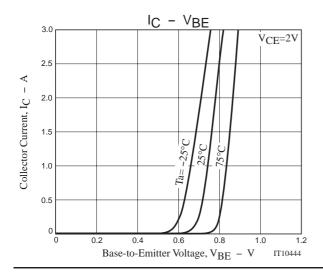
unit : mm 7019A-004

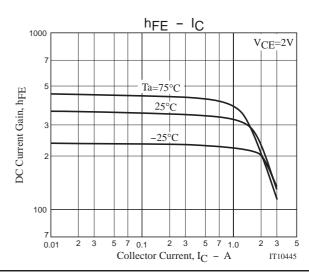


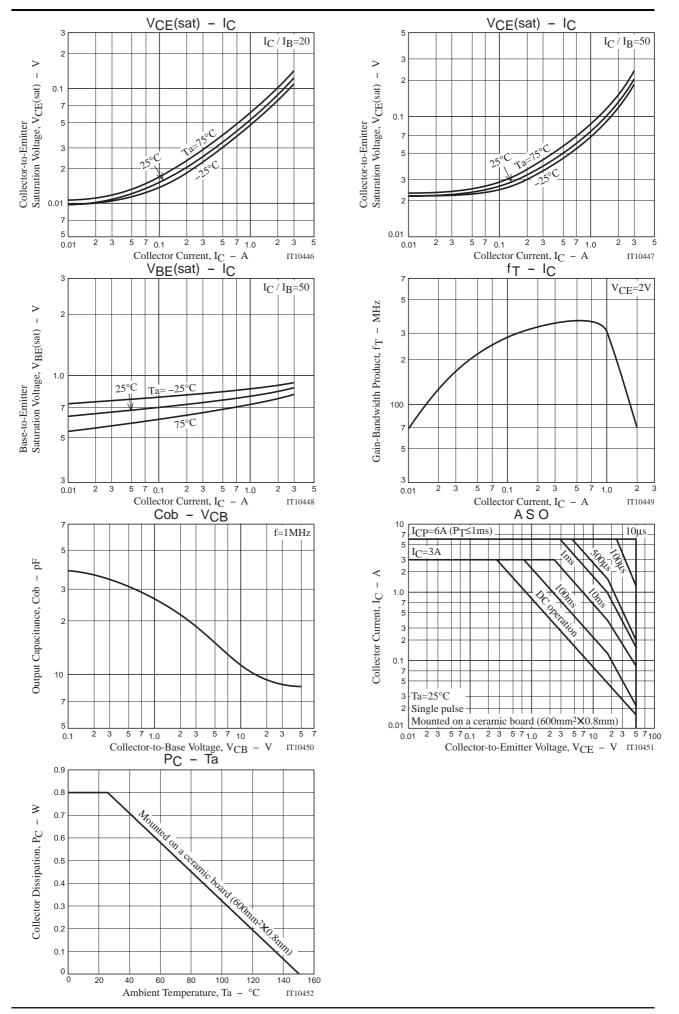
### **Switching Time Test Circuit**



 $I_{C}=10I_{B1}=-10I_{B2}=1A$ 







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